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TEOS characterization of 2D materials – from graphene to TMDCs

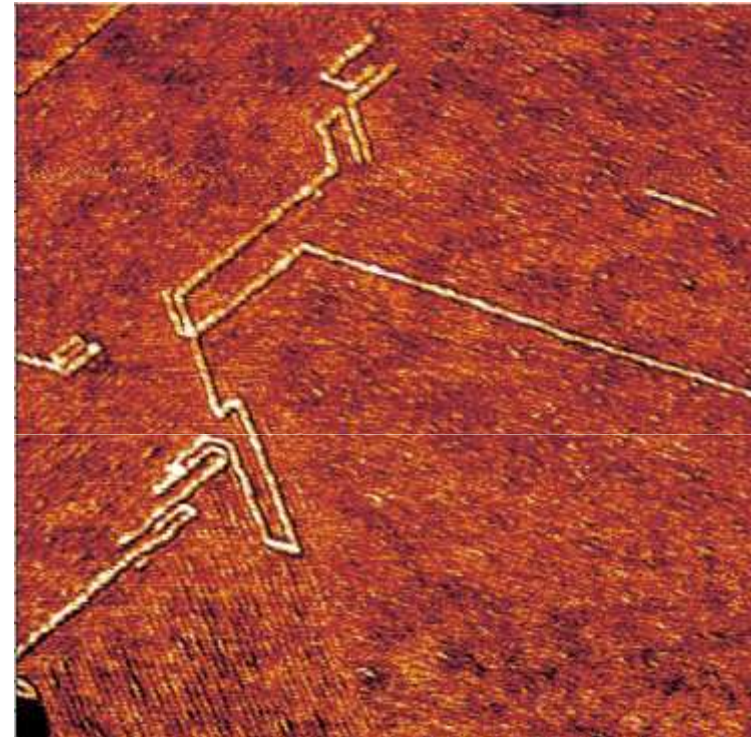
30-03-2017

Graphene2017

Bringing Scanning Probe Microscopies...

- SPM bring a lot of information on the physical characteristics of materials
 - *Topography*
 - *Mechanical properties*
 - *Electrical and magnetic properties*

- SPM is truly a nanoscale imaging technique...
 ...but it lacks ***chemical*** sensitivity



SS-DNA on HOPG functionalized with octadecylamine. 500nm frequency shift image.

... and Raman together

■ Confocal Raman Microscopy is a very *specific* chemical imaging

- Precise structural information, wide areas of application
- Non-destructive technique, compatible with many environments
- A wide spectrum of available laser sources
(from UV to IR : possibility of resonant Raman scattering)

■ Drawbacks

- Low cross-section ($\sim 10^{-30}$)
- Limited spatial resolution



Graphene- HORIBA

- 156 x 180 = 28080 spectra (step = 0.5 μ m)
- 2 min 08 (EMCCD, SWIFT; Acq. Time 2 ms + 1.5 ms)

Let's break the Rayleigh criterion!

How?

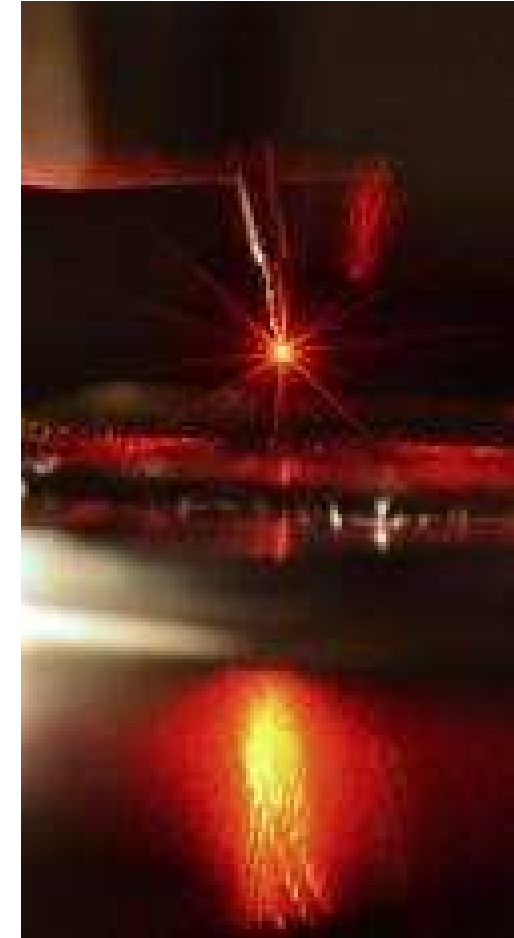


Nano Lightning Rod

plays the role of a Nano-Antenna

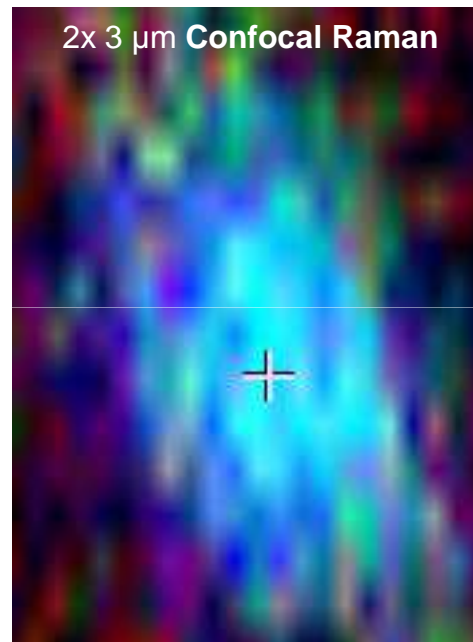
. Signal Enhancement

- *Near-Field Resolution*

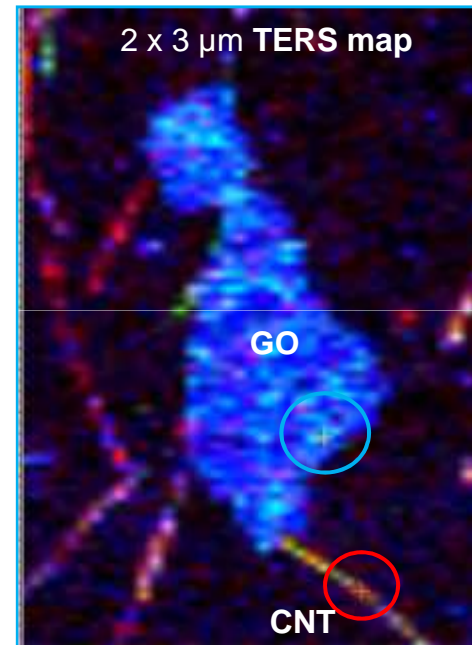
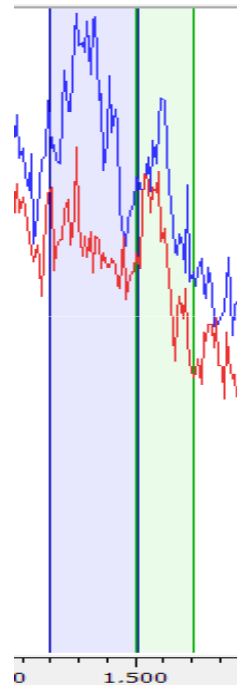


Conventional Raman VS TERS

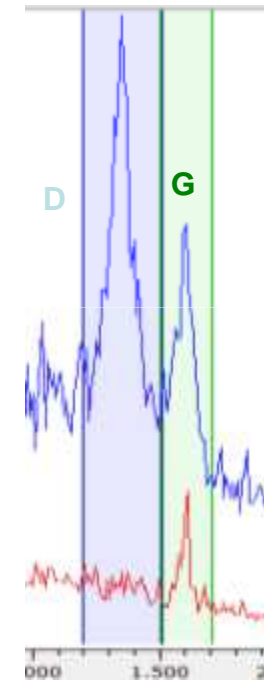
Confocal Raman and TERS of the same area, graphene oxide and CNTs on Au



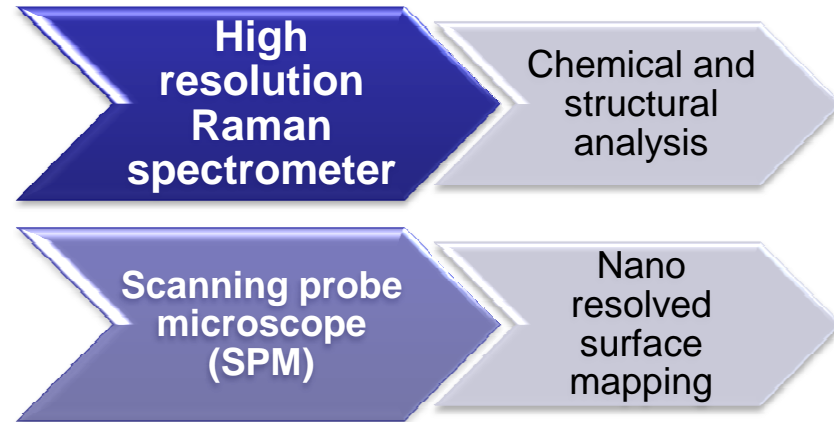
Confocal Raman
13 mW; integration 1 s



TERS
130 μW; integration 0.2 s



Bringing SPM and Raman together

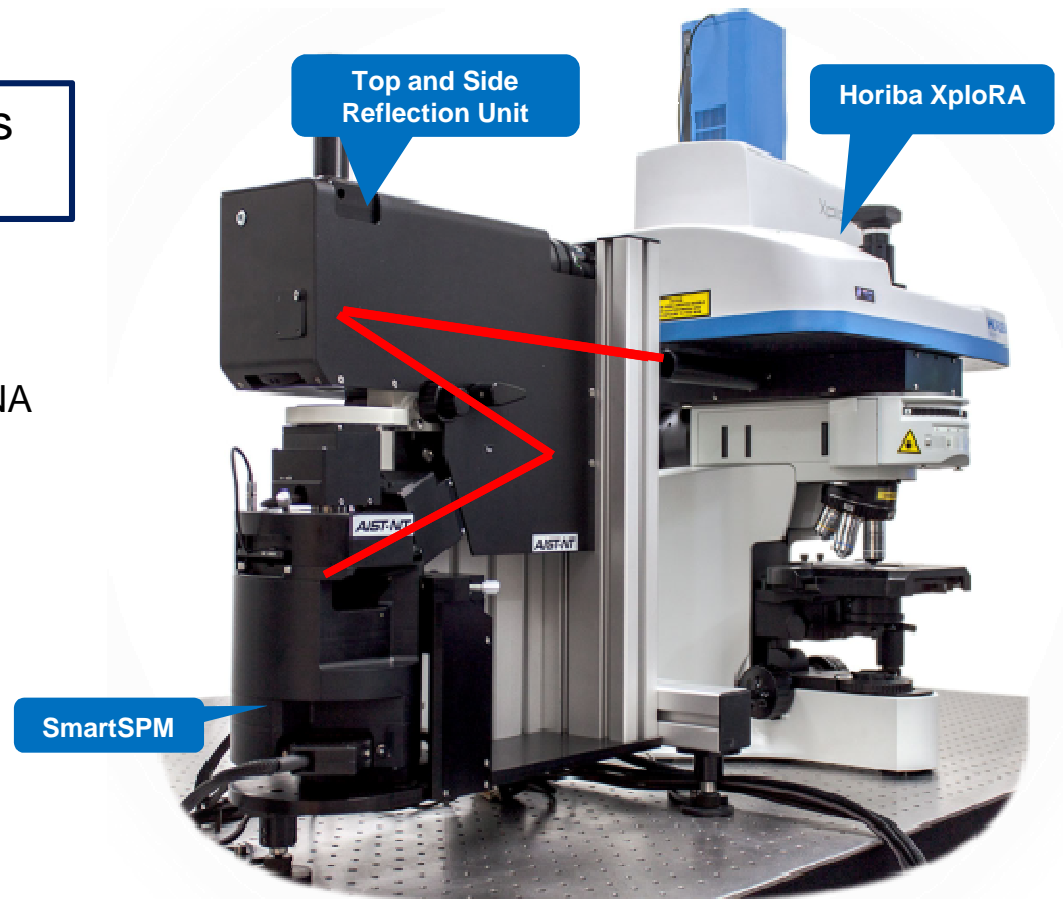
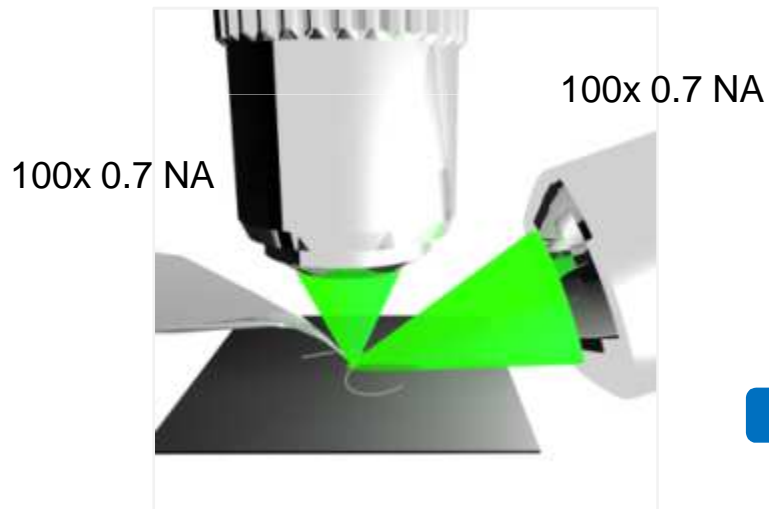


**Tip Enhanced Raman Spectroscopy (TERS)
aka NanoRaman
aka Near-field Raman Spectroscopy**

NanoRaman: Optical configurations

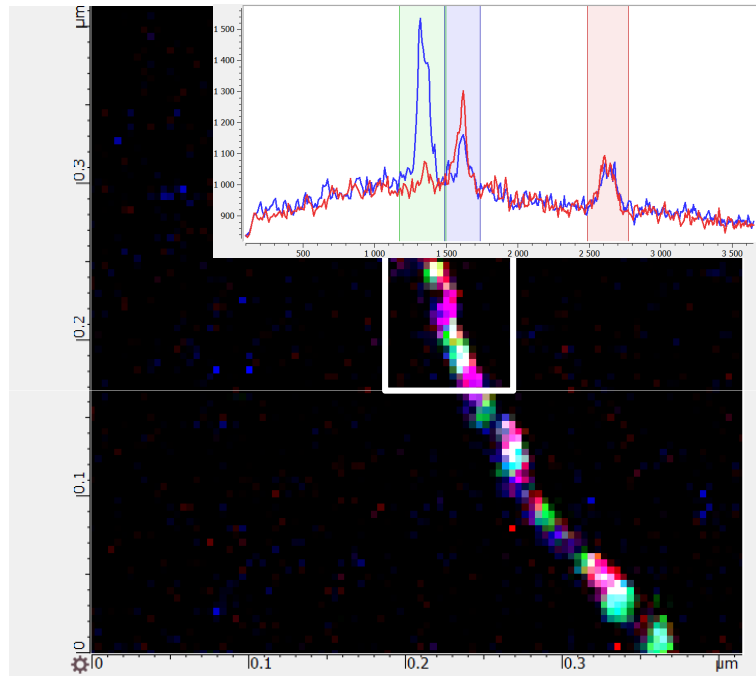
Top and Side illumination

- Top: co-localized measurements
- Side: optimized for TERS

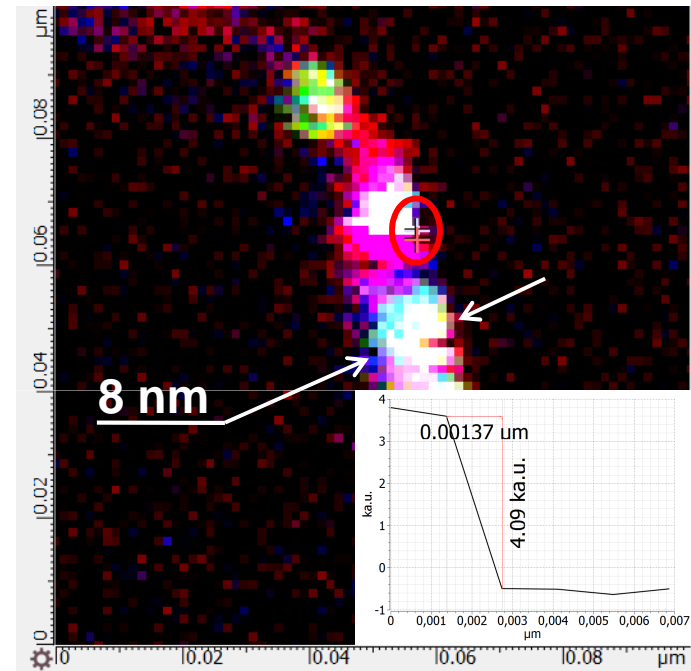


TERS: spatial resolution

CNTs maps out-of-lab conditions!



400 nm x 400 nm (100 x 100 pixels)

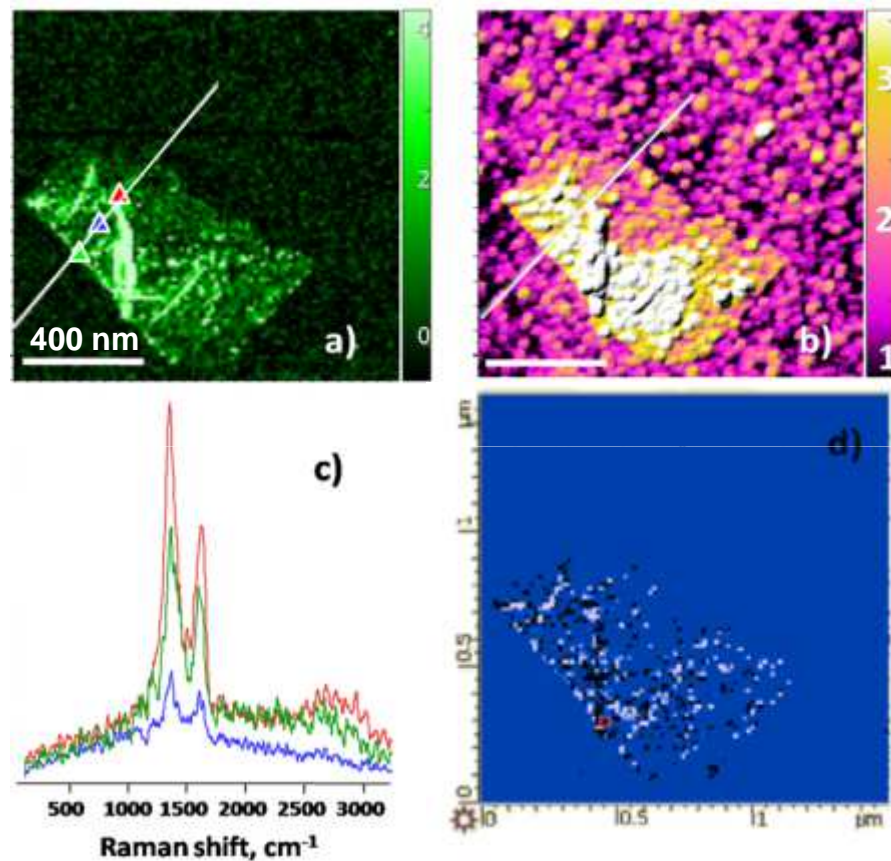


100 nm x 100 nm (75 x 75 pixels), 50 ms per pixel

Optical resolution capability: **8 nm**
Pixel step: **1.3 nm** → chemical sensitivity in both X and Y direction

Recorded @ SPIE San Diego, 2015

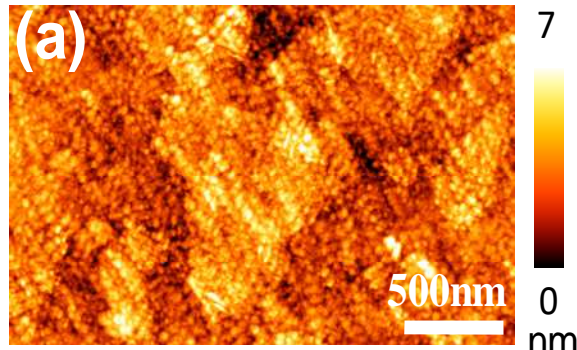
TERS Response of Graphene Oxide



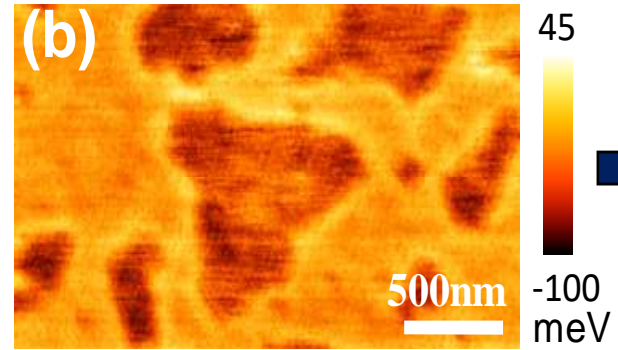
- a) 100 pixels per line TERS map of D-band intensity
- b) Topography image of the same flake
- c) representative TERS spectra
- d) **distribution of the ratio of G to D band intensities**

- Increase of both the D and G TERS band intensities at creases and wrinkles
- increase of TERS activity is not consequence of the increased thickness of the flake at folds

Combined TERS and KPFM mapping of GO-COOH

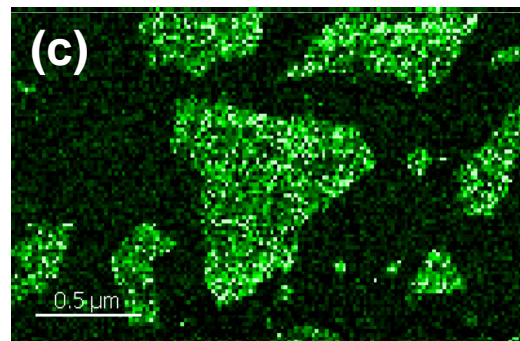


AFM topographic image

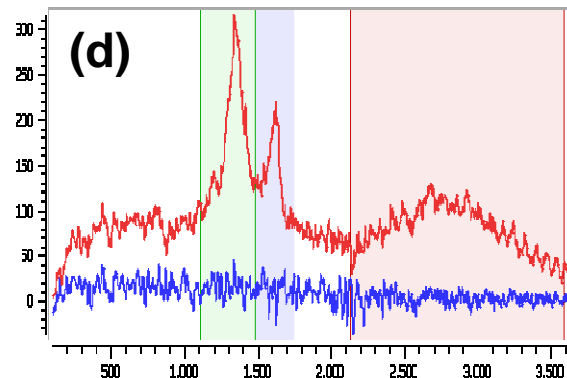


KPFM potential image

→ the calculated Fermi level of GO varies from 5eV to 5.14eV

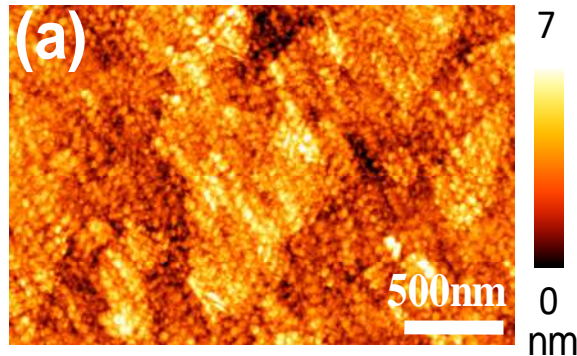


TERS image

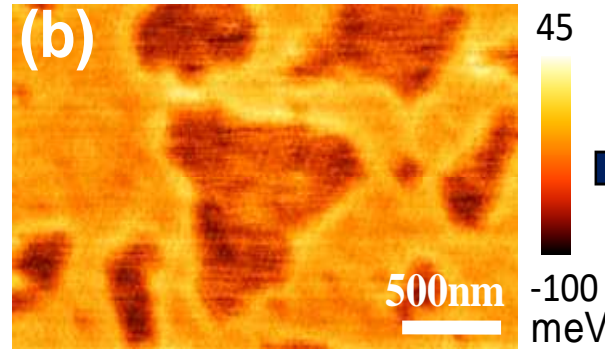


Typical TER spectra

Combined TERS and KPFM mapping of GO-COOH

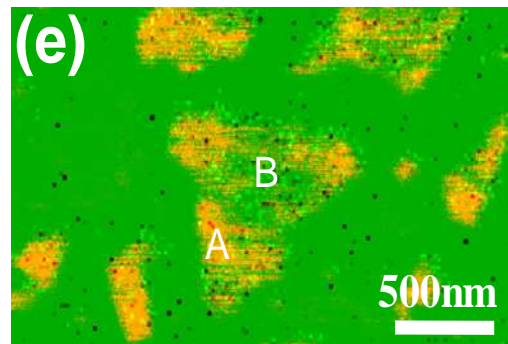


(a) AFM topographic image

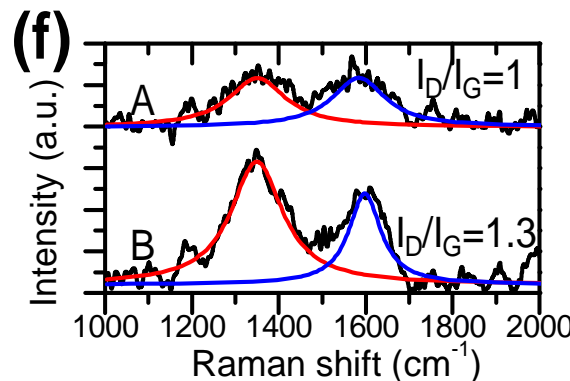


(b) KPFM potential image

the calculated Fermi level of GO varies from 5eV to 5.14eV



(e) Overlay image using I_D/I_G and inverse KPD



(f) average TERS spectra from region A and B

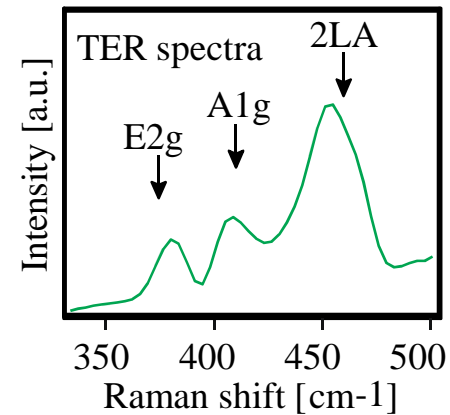
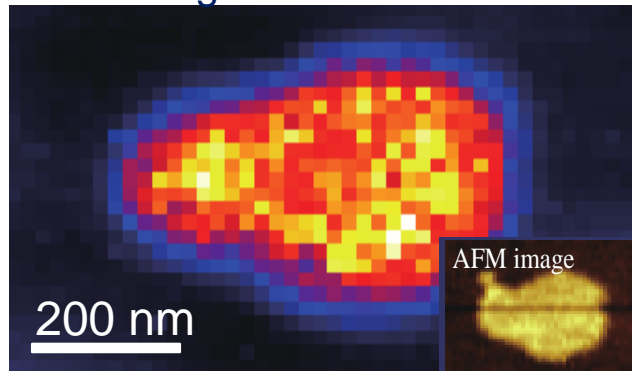
The high KPD areas always have high intensity of I_D/I_G , while low KPD areas always have low intensity of I_D/I_G

The Fermi level in an area of GO increases with I_D/I_G (ie with density of defects)

Non gap-mode TERS and TEPL: MoS₂

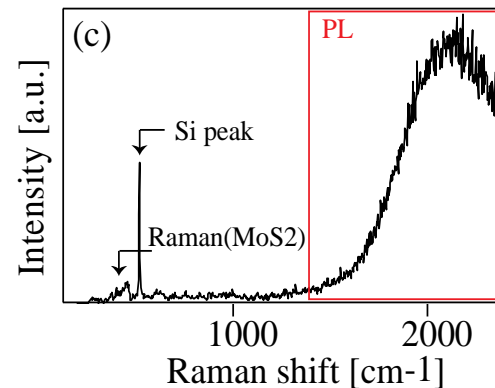
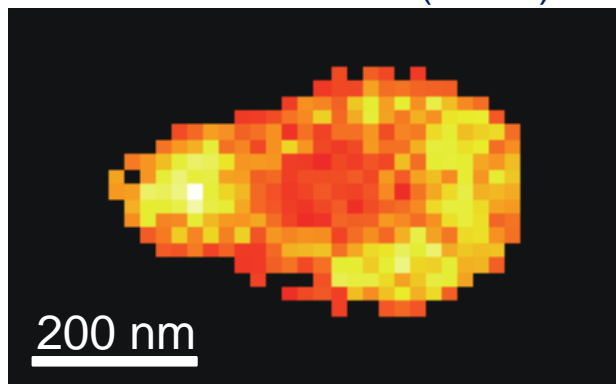
CVD grown MoS₂ on Si substrate, Ag tip, 594 nm, reflection configuration

TERS image



➔ **Monolayer flake**
(supported by the distance between the E2g and A1g).

TE Photoluminescence (TEPL) image

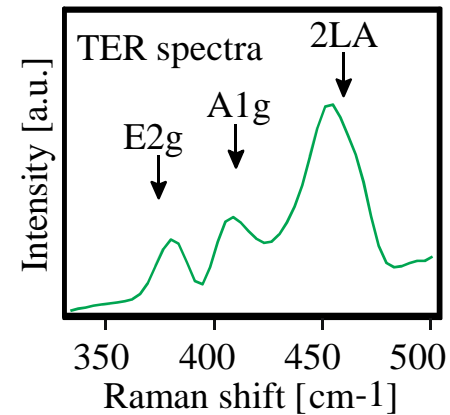
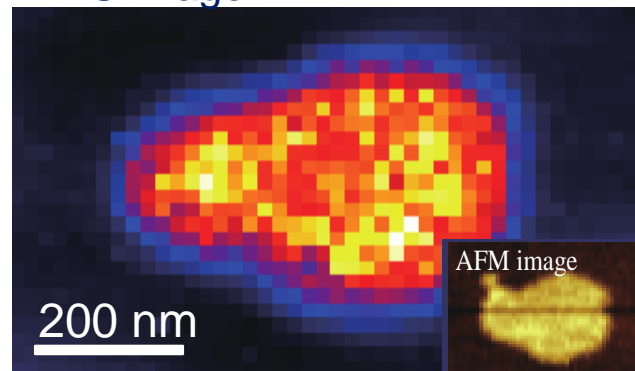


➔ **Excitonic emission is enhanced around the edges**

Non gap-mode TERS and TEPL: MoS₂

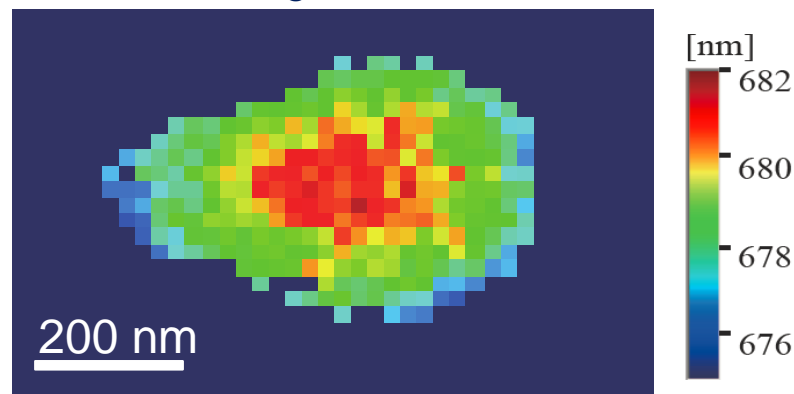
CVD grown MoS₂ on Si substrate, Ag tip, 594 nm, reflection configuration

TERS image



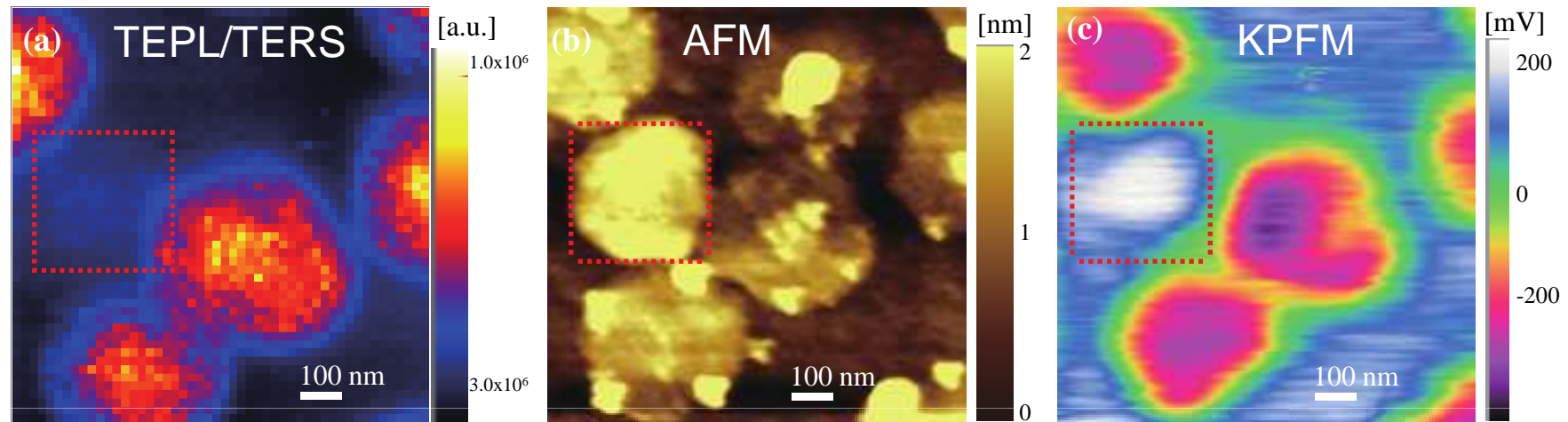
➔ **Monolayer flake**
(supported by the distance between the E2g and A1g).

TEPL shift image



➔ **Edge-induced modification in the Fermi level of the MoS₂ ML flake**

Combined TERS and KPFM mapping of MoS₂



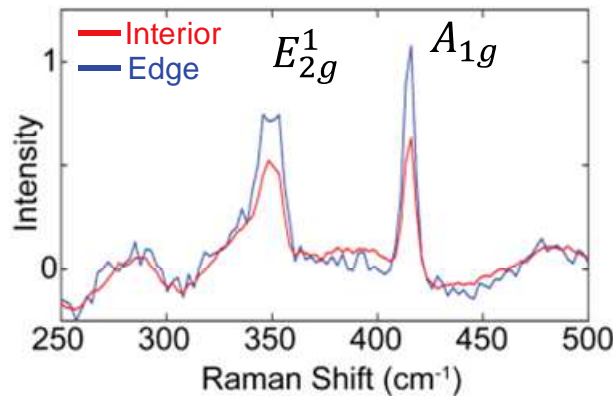
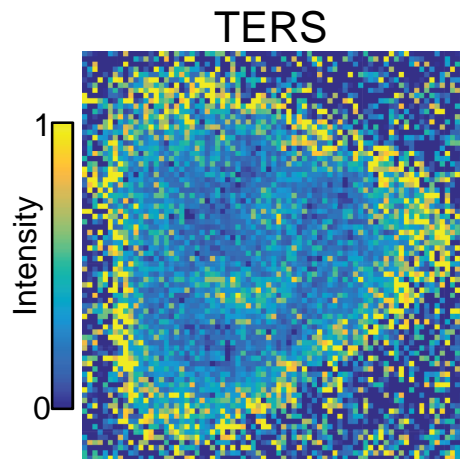
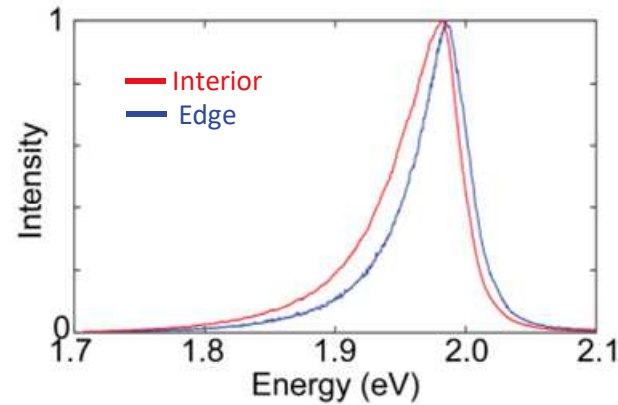
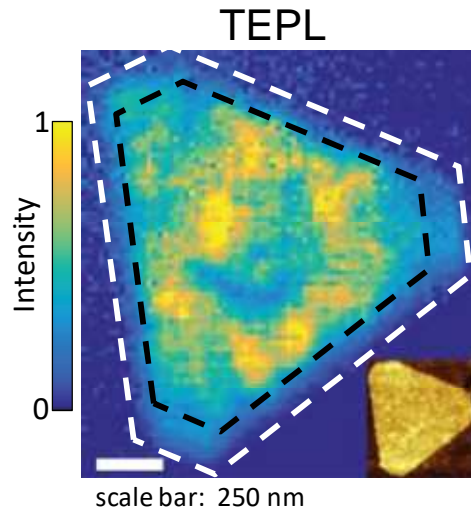
(a) TEPL map, (b) AFM image of monolayer and bilayer MoS₂ flakes and (c) Kelvin Force image of the same area

- ➔ PL intensity, and TERS (through separation between A1g and E2g peaks) are consistent in distinguishing monolayer and bilayer flakes
- ➔ Kelvin probe force map shows positive values (~100 mV) for bilayer flakes and negative values around -300 mV for monolayer flakes.
→the Fermi energy increases in bilayer MoS₂.

Non gap-mode TERS: WS₂

→ extend the TERS technique to others 2D TMDs:

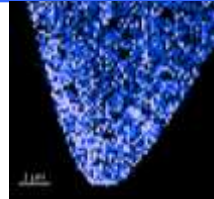
- CVD grown WS₂ on Si substrate
- Ag tips, 638 nm
- Reflection configuration



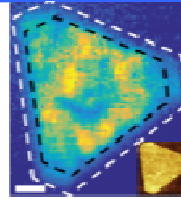
**Monolayer WS₂
edges vs interior:
spectral signatures
of different doping**

CONCLUSIONS

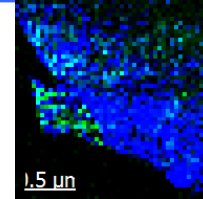
TERS and 2D materials



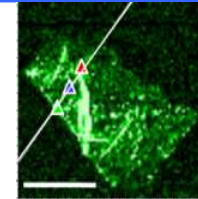
MoS₂



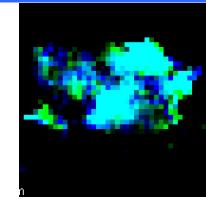
WS₂



WSe₂



GO



BiOCl

- **TERS IS READY** for real-life analytical application on number of scientifically interesting samples.
- Without detailed NANOSCALE characterization of 1-d and 2D materials, their use in next generation devices is pretty much impossible.
TERS can provide reliable information on peculiarities of local structure with resolution below 10 nm.
- TERS is extended to two-dimensional materials with dominating out-of-plane Raman-active modes such as WS₂, MoS₂, WSe₂ ...

**AFM (topographic/structural) + TERS (chemical) + TEPL (optoelectronic)
+ KPFM / cAFM (local work function / local conductivity)**

Thank you very much for your attention.

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